## 1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- · Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV

## 3. Applications

- Relay driver
- · High-speed line driver
- High-side loadswitch
- · Switching circuits

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V	
$V_{GS}$	gate-source voltage			-8	-	8	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-550	mA	
Static characte	Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -400 \text{ mA}; T_j = 25 \text{ °C}$		-	0.67	0.85	Ω	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



20 V, 550 mA dual P-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	6 5 4	D1 D2
2	G1	gate TR1	6 5 4	
3	D2	drain TR2		$G1$ $\Psi$ $\Psi$ $G2$
4	S2	source TR2		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	SOT666	S1 S2 017aaa260

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PMDT670UPE	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	SOT666		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMDT670UPE	AG

#### 20 V, 550 mA dual P-channel Trench MOSFET

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-550	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-350	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T <sub>sp</sub> = 25 °C		-	1090	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					-
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-370	mA
ESD maxim	um rating			'	'	'
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

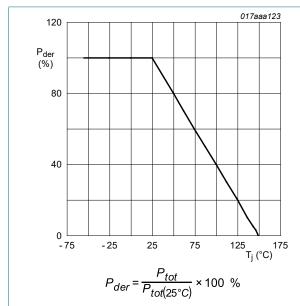


Fig. 1. Normalized total power dissipation as a function of junction temperature

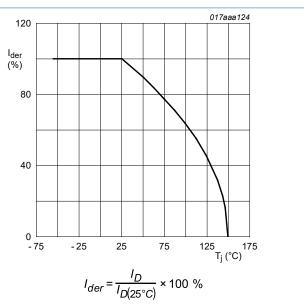


Fig. 2. Normalized continuous drain current as a function of junction temperature

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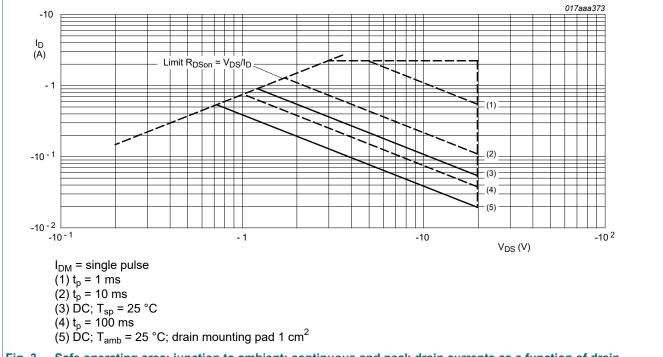


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 20 V, 550 mA dual P-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor		,				
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	330	380	K/W
junction to ambien	junction to ambient		[2]	-	280	320	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	115	K/W
Per device	'		,				
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

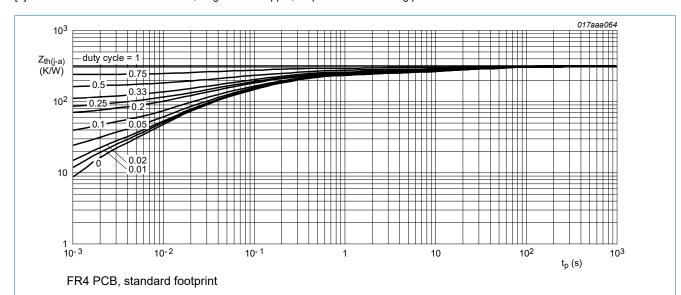


Fig. 4. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

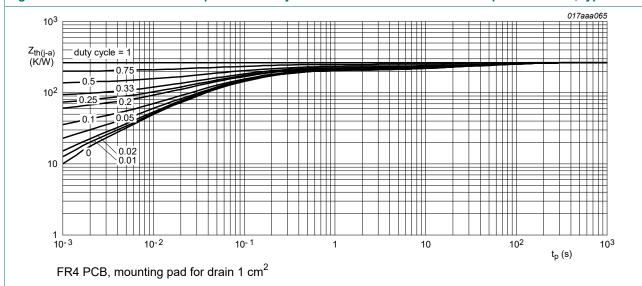


Fig. 5. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 20 V, 550 mA dual P-channel Trench MOSFET

## 10. Characteristics

## **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.5	-0.8	-1.3	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.5	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-0.5	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -400 mA; $T_j$ = 25 °C	-	0.67	0.85	Ω
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -400 \text{ mA}; T_j = 150 ^{\circ}\text{C}$	-	1.1	1.4	Ω
		$V_{GS}$ = -2.5 V; $I_D$ = -200 mA; $T_j$ = 25 °C	-	1.2	1.5	Ω
		$V_{GS}$ = -1.8 V; $I_D$ = -10 mA; $T_j$ = 25 °C	-	1.8	2.8	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -200 mA; $T_j$ = 25 °C	-	610	-	mS
Dynamic ch	naracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -400 mA;	-	0.76	1.14	nC
Q <sub>GS</sub>	gate-source charge	V <sub>GS</sub> = -4.5 V; T <sub>j</sub> = 25 °C	-	0.28	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	0.18	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	58	87	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	21	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	12	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \text{ V}; R_L = 250 \Omega; V_{GS} = -4.5 \text{ V};$	-	18	36	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	80	160	ns
t <sub>f</sub>	fall time	1 – – – – – – – – – – – – – – – – – – –	-	72	-	ns
Source-drai	in diode (per transistor)		L	1		1
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -300 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-0.48	-0.84	-1.2	V

### 20 V, 550 mA dual P-channel Trench MOSFET

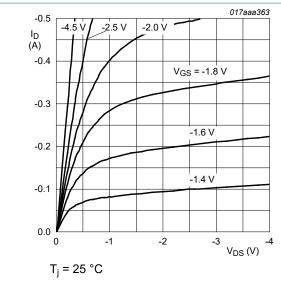
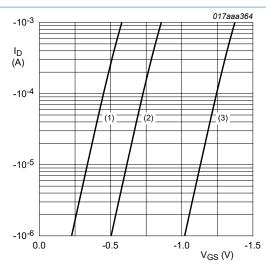


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



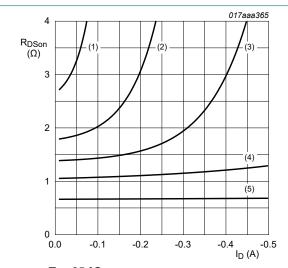
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $T_i = 25 \,^{\circ}C$ 

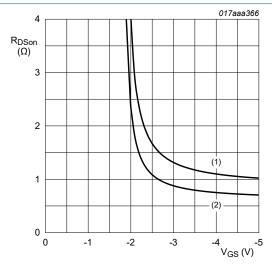
 $(1) V_{GS} = -1.5 V$ 

 $(2) V_{GS} = -1.8 V$ 

(3)  $V_{GS} = -2.0 \text{ V}$ (4)  $V_{GS} = -2.5 \text{ V}$ 

 $(5) V_{GS} = -4.5 V$ 





 $I_D = -400 \text{ mA}$ (1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \,^{\circ}\text{C}$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 20 V, 550 mA dual P-channel Trench MOSFET

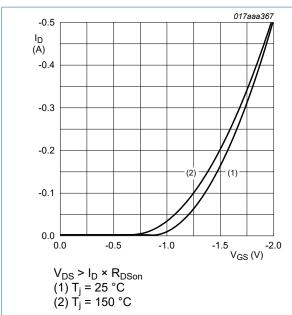


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

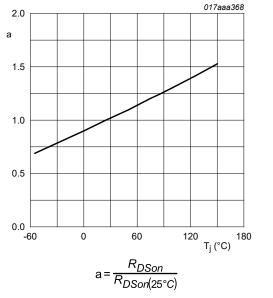
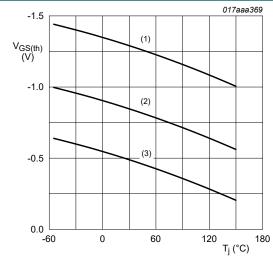


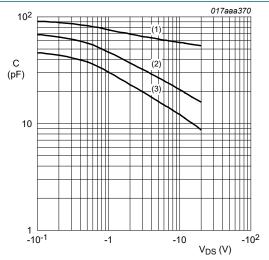
Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 20 V, 550 mA dual P-channel Trench MOSFET

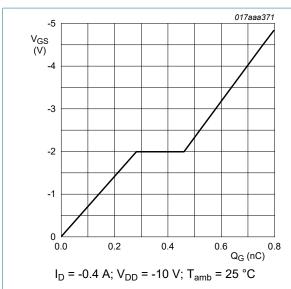


Fig. 14. Gate-source voltage as a function of gate charge; typical values

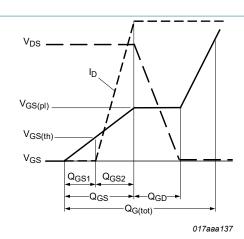
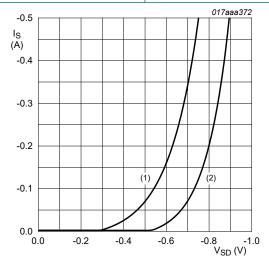


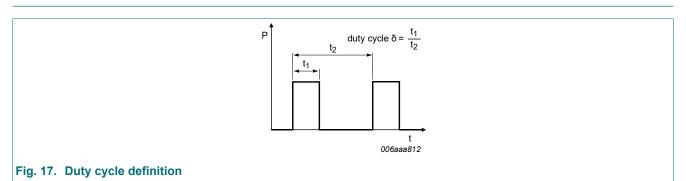
Fig. 15. Gate charge waveform definitions



V<sub>GS</sub> = 0 V (1) T<sub>amb</sub> = 150 °C (2) T<sub>amb</sub> = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



#### 20 V, 550 mA dual P-channel Trench MOSFET

# 12. Package outline

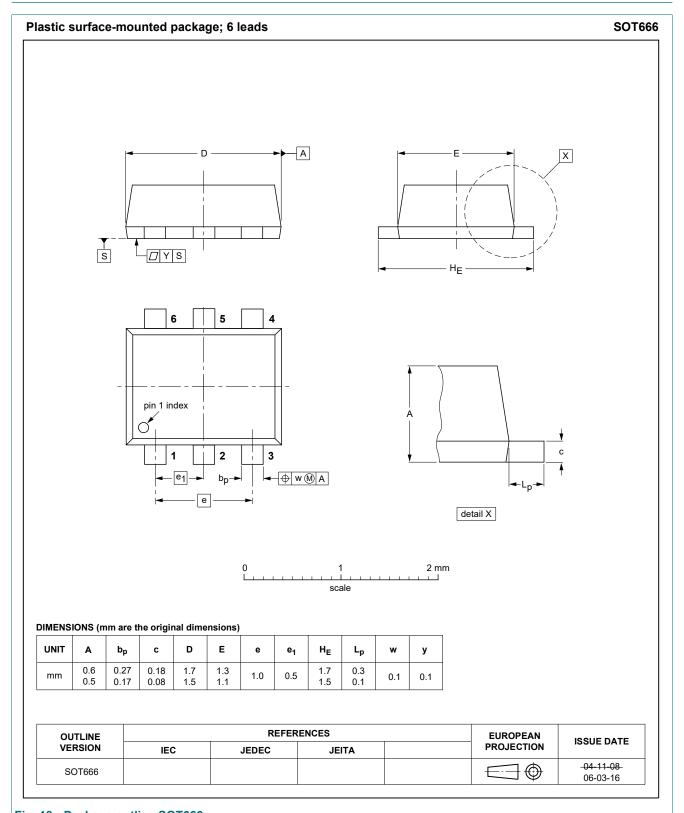
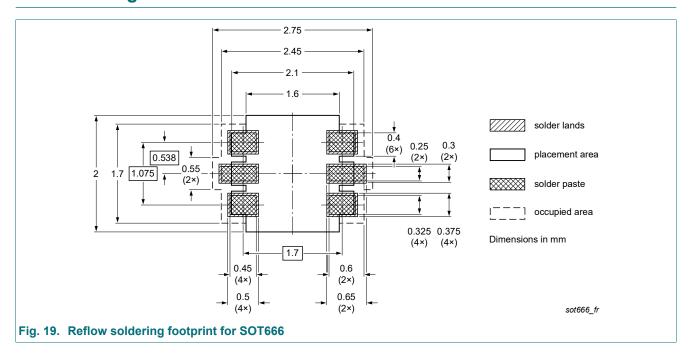


Fig. 18. Package outline SOT666

## 20 V, 550 mA dual P-channel Trench MOSFET

# 13. Soldering



## 20 V, 550 mA dual P-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Table 0. Itevision ins	otor y						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMDT670UPE v.2	20221228	Product data sheet	-	PMDT670UPE v.1			
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia</li> <li>Legal texts have been adapted to the new company name where appropriate</li> <li>Product changed to non-automotive qualification</li> </ul>						
PMDT670UPE v.1	20110913	Product data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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